

**WARP2 SERIES IGBT WITH ULTRAFAST SOFT RECOVERY DIODE**
**Features**

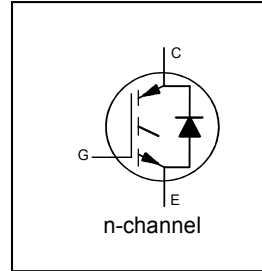
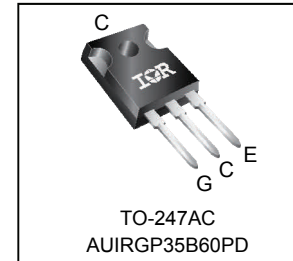
- NPT Technology, Positive Temperature Coefficient
- Lower  $V_{CE(SAT)}$
- Lower Parasitic Capacitances
- Minimal Tail Current
- HEXFRED Ultra Fast Soft-Recovery Co-Pack Diode
- Tighter Distribution of Parameters
- Higher Reliability
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

**Applications**

- PFC and ZVS SMPS Circuits
- DC/DC Converter Charger

**Benefits**

- Parallel Operation for Higher Current Applications
- Lower Conduction Losses and Switching Losses
- Higher Switching Frequency up to 150kHz


 $V_{CES} = 600V$   
 $V_{CE(on)} \text{ typ.} = 1.85V$   
 @  $V_{GE} = 15V$   $I_C = 22A$ 
**Equivalent MOSFET Parameters<sup>①</sup>**
 $R_{CE(on)} \text{ typ.} = 84m\Omega$   
 $I_D$  (FET equivalent) = 35A


G	C	E
Gate	Collector	Emitter

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGP35B60PD	TO-247AC	Tube	25	AUIRGP35B60PD

**Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	60	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	34	
$I_{CM}$	Pulse Collector Current (Ref. Fig. C. T.4)	120	
$I_{LM}$	Clamped Inductive Load Current <sup>②</sup>	120	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	40	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	15	
$I_{FSM}$	Maximum Repetitive Forward Current	60	
$V_{GE}$	Gate-to-Emitter Voltage	±20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	308	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	123	
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in.(1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf-in (1.1 N·m)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (each IGBT)	—	—	0.41	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case (each Diode)	—	—	1.7	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.50	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	—	40	
	Weight	—	6.0(0.21)	—	g(oz)

\* Qualification standards can be found at [www.infineon.com](http://www.infineon.com)

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

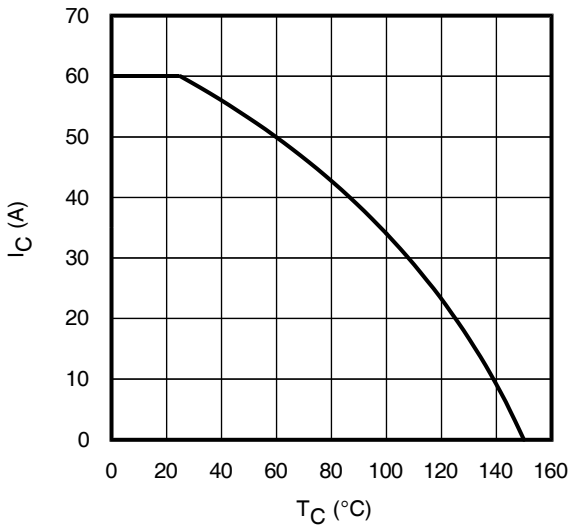
	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref. Fig.
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 500μA	
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.78	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA (25°C-125°C)	
R <sub>G</sub>	Internal Gate Resistance	—	1.7	—	Ω	1MHz, Open Collector	4,5,6,8,9
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.85	2.15	V	I <sub>C</sub> = 22A, V <sub>GE</sub> = 15V	
		—	2.25	2.55		I <sub>C</sub> = 35A, V <sub>GE</sub> = 15V	
		—	2.37	2.80		I <sub>C</sub> = 22A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 125°C	
		—	3.00	3.45		I <sub>C</sub> = 35A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 125°C	
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	4.0	5.0	V	I <sub>C</sub> = 250μA	7,8,9
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Threshold Voltage temp. coefficient	—	-10	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0mA	
g <sub>fe</sub>	Forward Transconductance	—	36	—	S	V <sub>CE</sub> = 50V, I <sub>C</sub> = 22A, PW = 80μs	
I <sub>CES</sub>	Collector-to-Emitter Leakage Current	—	3.0	375	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V	
		—	0.35	—	mA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 125°C	
V <sub>FM</sub>	Diode Forward Voltage Drop	—	1.30	1.70	V	I <sub>F</sub> = 15A	10
		—	1.20	1.60		I <sub>F</sub> = 15A, T <sub>J</sub> = 125°C	
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0V	

**Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

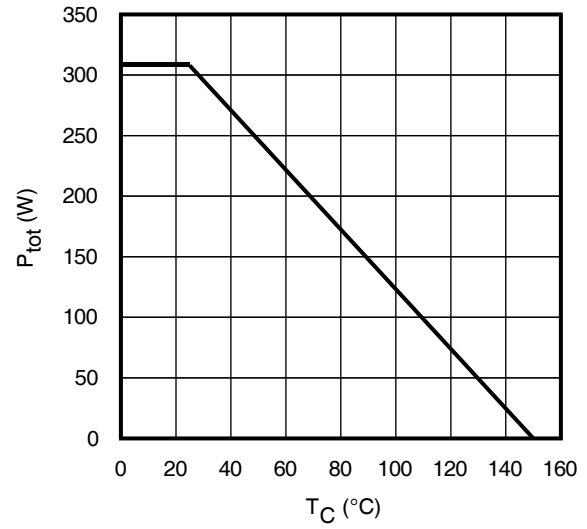
	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref. Fig.
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	160	240	nC	I <sub>C</sub> = 22A V <sub>GE</sub> = 15V V <sub>CC</sub> = 400V	17
Q <sub>ge</sub>	Gate-to-Emitter Charge (turn-on)	—	55	83			CT1
Q <sub>gc</sub>	Gate-to-Collector Charge (turn-on)	—	21	32			
E <sub>on</sub>	Turn-On Switching Loss	—	220	270	μJ	I <sub>C</sub> = 22A, V <sub>CC</sub> = 390V, V <sub>GE</sub> = +15V, R <sub>G</sub> = 3.3Ω, L = 200μH, T <sub>J</sub> = 25°C ④	CT3
E <sub>off</sub>	Turn-Off Switching Loss	—	215	265			
E <sub>total</sub>	Total Switching Loss	—	435	535	μJ	I <sub>C</sub> = 22A, V <sub>CC</sub> = 390V, V <sub>GE</sub> = +15V, R <sub>G</sub> = 3.3Ω, L = 200μH, T <sub>J</sub> = 125°C ④	CT3 11,13 WF1,WF2
t <sub>d(on)</sub>	Turn-On delay time	—	26	34			
t <sub>r</sub>	Rise time	—	6.0	8.0	ns	I <sub>C</sub> = 22A, V <sub>CC</sub> = 390V, V <sub>GE</sub> = +15V, R <sub>G</sub> = 3.3Ω, L = 200μH, T <sub>J</sub> = 125°C ④	CT3 12,14 WF1,WF2
t <sub>d(off)</sub>	Turn-Off delay time	—	110	122			
t <sub>f</sub>	Fall time	—	8.0	10	μJ	I <sub>C</sub> = 22A, V <sub>CC</sub> = 390V, V <sub>GE</sub> = +15V, R <sub>G</sub> = 3.3Ω, L = 200μH, T <sub>J</sub> = 125°C ④	CT3 11,13 WF1,WF2
E <sub>on</sub>	Turn-On Switching Loss	—	410	465			
E <sub>off</sub>	Turn-Off Switching Loss	—	330	405	ns	I <sub>C</sub> = 22A, V <sub>CC</sub> = 390V, V <sub>GE</sub> = +15V, R <sub>G</sub> = 3.3Ω, L = 200μH, T <sub>J</sub> = 125°C ④	CT3 12,14 WF1,WF2
E <sub>total</sub>	Total Switching Loss	—	740	870			
t <sub>d(on)</sub>	Turn-On delay time	—	26	34	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V f = 1.0Mhz	16
t <sub>r</sub>	Rise time	—	8.0	11			
t <sub>d(off)</sub>	Turn-Off delay time	—	130	150	pF	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 0V to 480V	15
t <sub>f</sub>	Fall time	—	12	16			
C <sub>ies</sub>	Input Capacitance	—	3715	—	A	T <sub>J</sub> = 150°C, I <sub>C</sub> = 120A V <sub>CC</sub> = 480V, V <sub>p</sub> ≤ 600V R <sub>g</sub> = 22Ω, V <sub>GE</sub> = +15V to 0V	3 CT2
C <sub>oes</sub>	Output Capacitance	—	265	—			
C <sub>res</sub>	Reverse Transfer Capacitance	—	47	—			
C <sub>oes eff.</sub>	Effective Output Capacitance (Time Related)	—	135	—			
C <sub>oes eff. (ER)</sub>	Effective Output Capacitance (Energy Related)	—	179	—	ns	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	19
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE					
t <sub>rr</sub>	Diode Reverse Recovery Time	—	42	60	nA	I <sub>F</sub> = 15A, V <sub>R</sub> = 200V, di/dt = 200A/μs	21
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	80	180			
I <sub>rr</sub>	Peak Reverse Recovery Current	—	220	600	A	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	19,20,21,22 CT5
		—	4.0	6.0			
		—	6.5	10			

**Notes:**

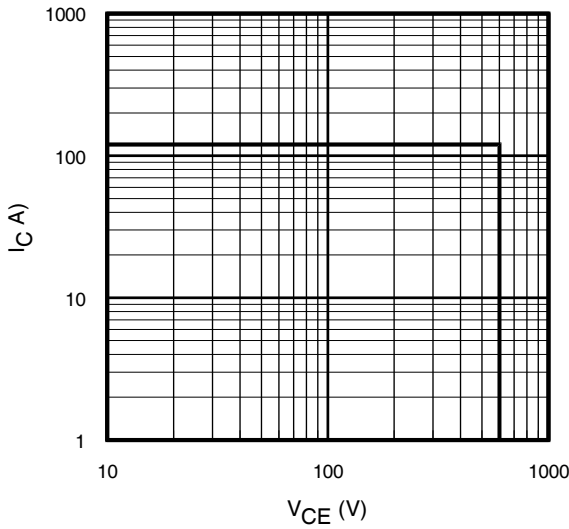
- R<sub>CE(on)</sub> typ. = equivalent on-resistance = V<sub>CE(on)</sub> typ. / I<sub>C</sub>, where V<sub>CE(on)</sub> typ. = 1.85V and I<sub>C</sub> = 22A. I<sub>D</sub> (FET Equivalent) is the equivalent MOSFET I<sub>D</sub> rating @ 25°C for applications up to 150kHz. These are provided for comparison purposes (only) with equivalent MOSFET solutions.
- V<sub>CC</sub> = 80% (V<sub>CES</sub>), V<sub>GE</sub> = 20V, L = 28 μH, R<sub>G</sub> = 22 Ω
- Pulse width limited by max. junction temperature.
- Energy losses include "tail" and diode reverse recovery, Data generated with use of Diode 30ETH06.
- C<sub>oes eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oes</sub> while V<sub>CE</sub> is rising from 0 to 80% V<sub>CES</sub>.  
C<sub>oes eff. (ER)</sub> is a fixed capacitance that stores the same energy as C<sub>oes</sub> while V<sub>CE</sub> is rising from 0 to 80% V<sub>CES</sub>.



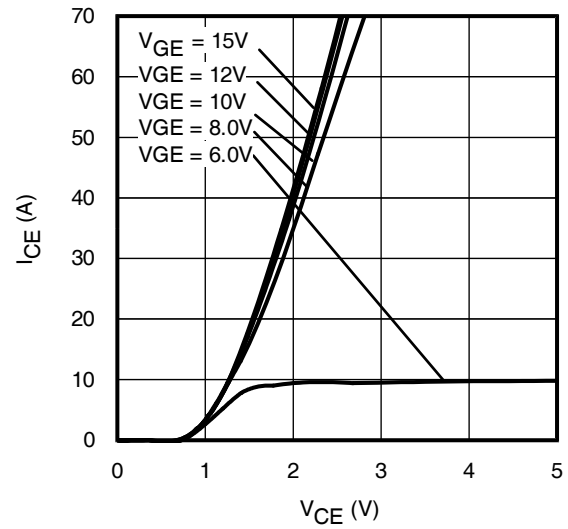
**Fig. 1** - Maximum DC Collector Current vs. Case Temperature



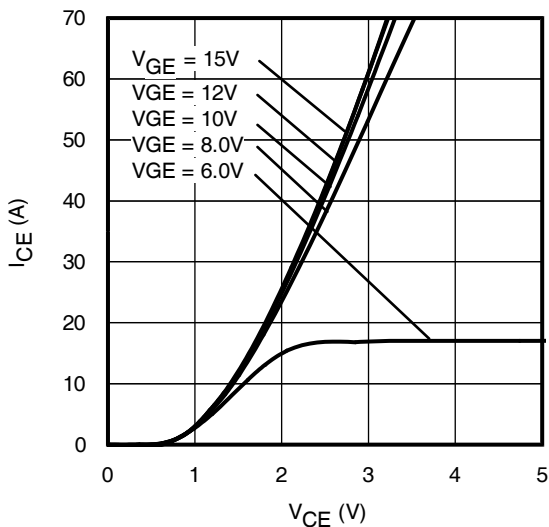
**Fig. 2** - Power Dissipation vs. Case Temperature



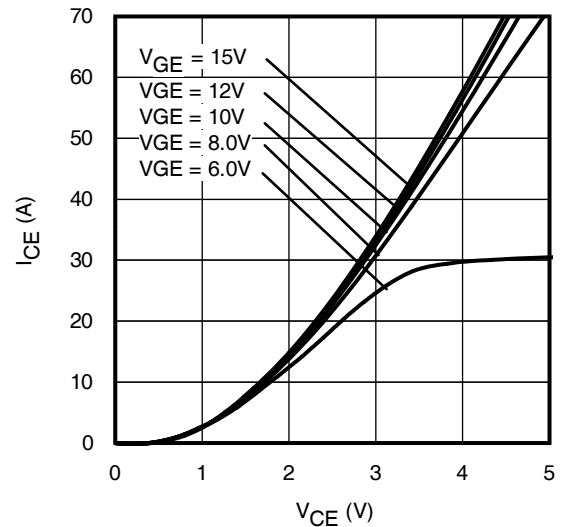
**Fig. 3** - Reverse Bias SOA  
 $T_J = 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$



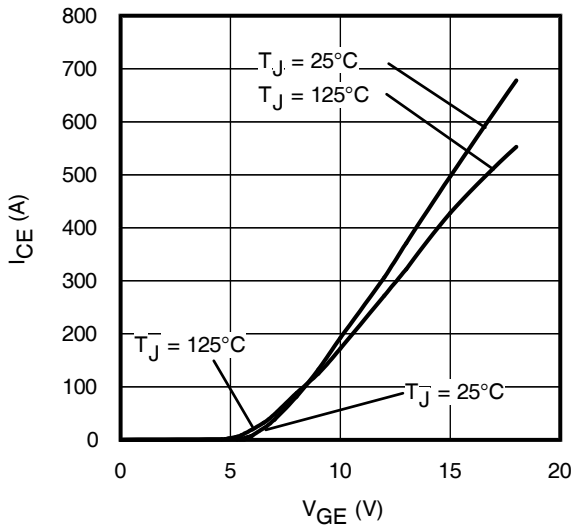
**Fig. 4** - Typ. IGBT Output Characteristics  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



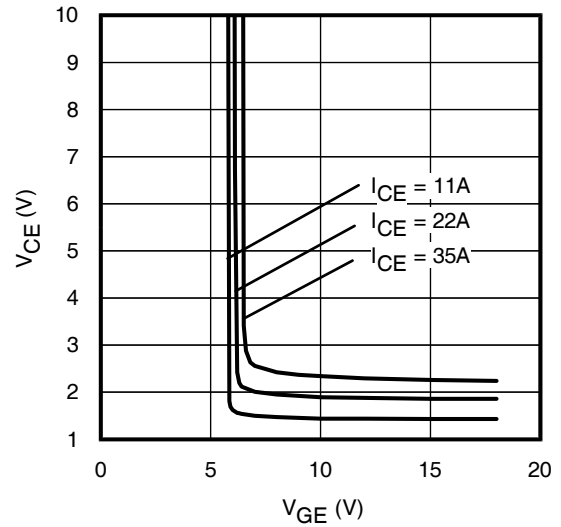
**Fig. 5** - Typ. IGBT Output Characteristics  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



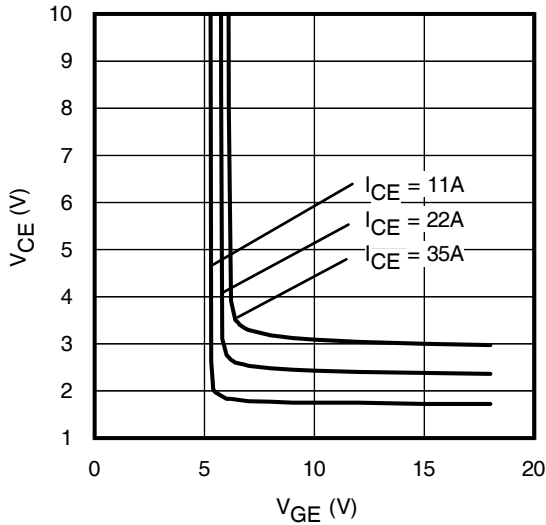
**Fig. 6** - Typ. IGBT Output Characteristics  
 $T_J = 125^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



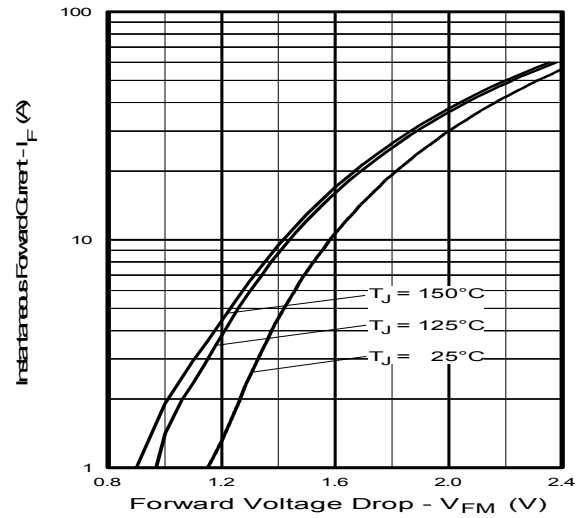
**Fig. 7 - Typ. Transfer Characteristics**  
 $V_{CE} = 50V$ ;  $t_p = 10\mu s$



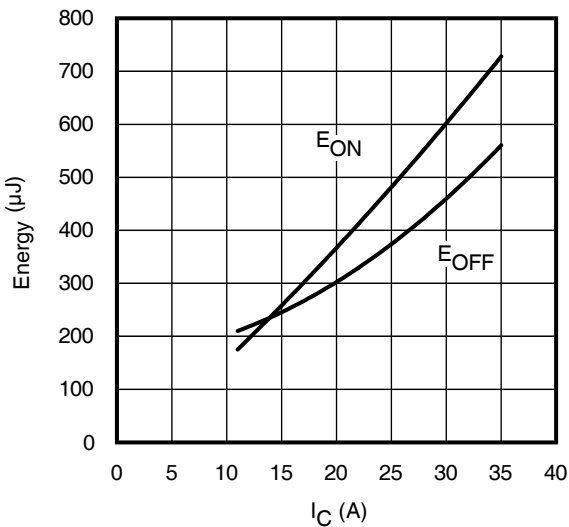
**Fig. 8 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = 25^\circ C$



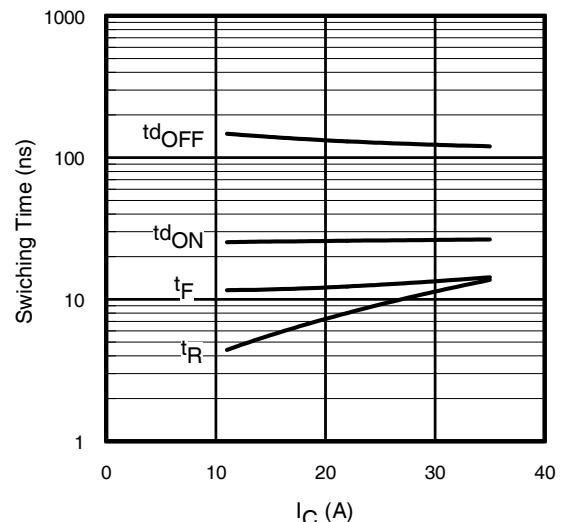
**Fig. 9 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = 125^\circ C$



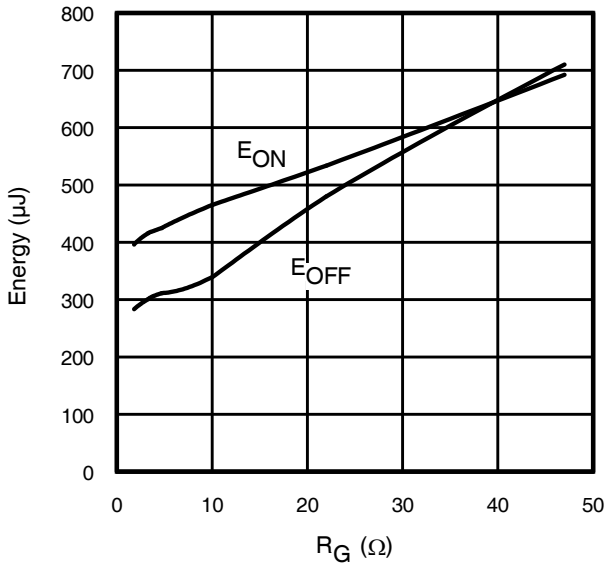
**Fig. 10 - Typ. Diode Forward Characteristics**  
 $t_p = 80\mu s$



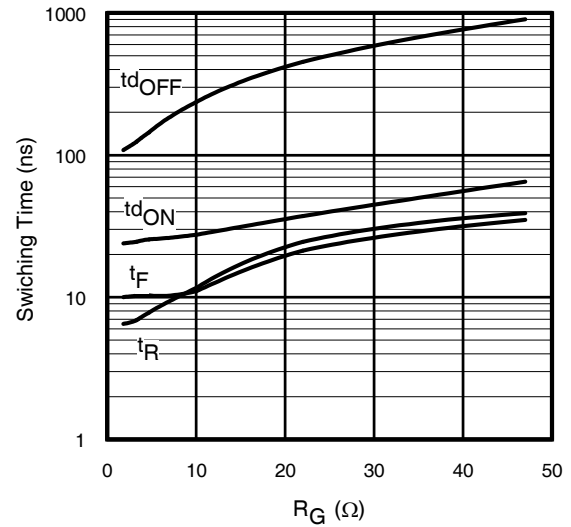
**Fig. 11 - Typ. Energy Loss vs.  $I_C$**   
 $T_J = 125^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 390V$ ,  $R_G = 3.3\Omega$ ;  $V_{GE} = 15V$ .  
 Diode clamp used: 30ETH06 (See C.T.3)



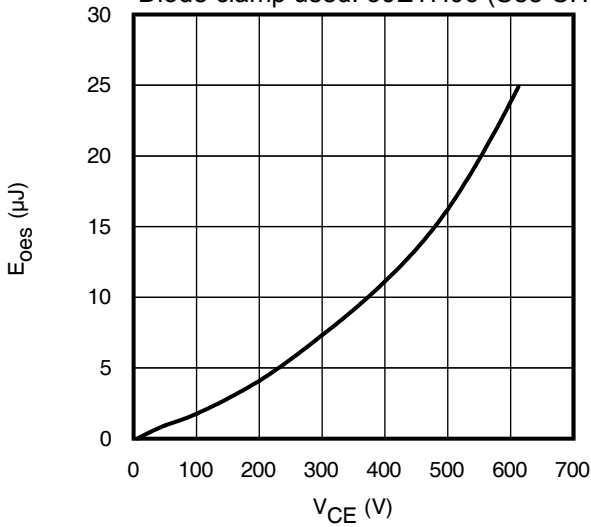
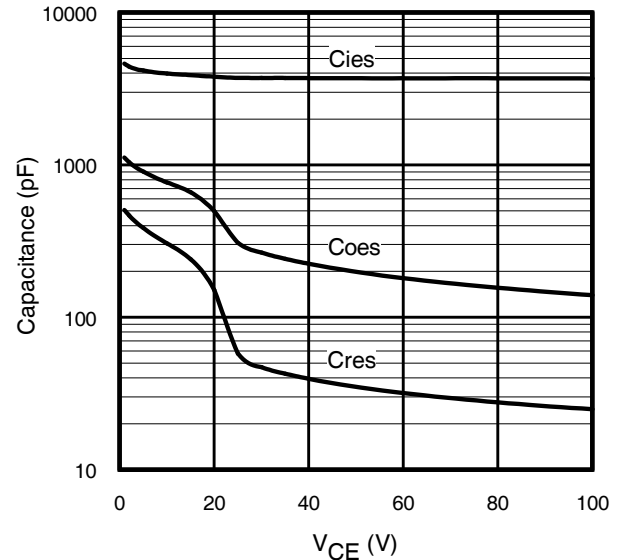
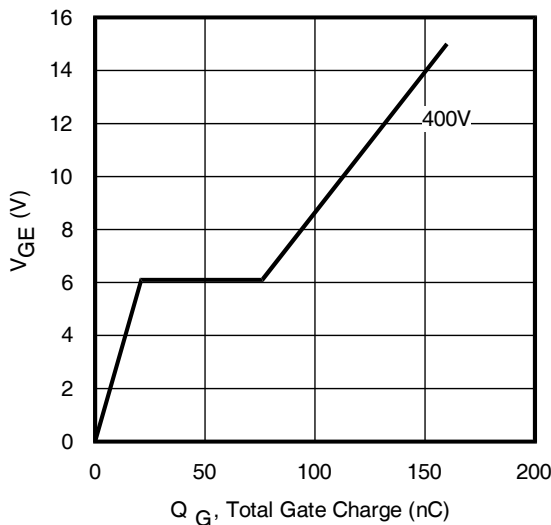
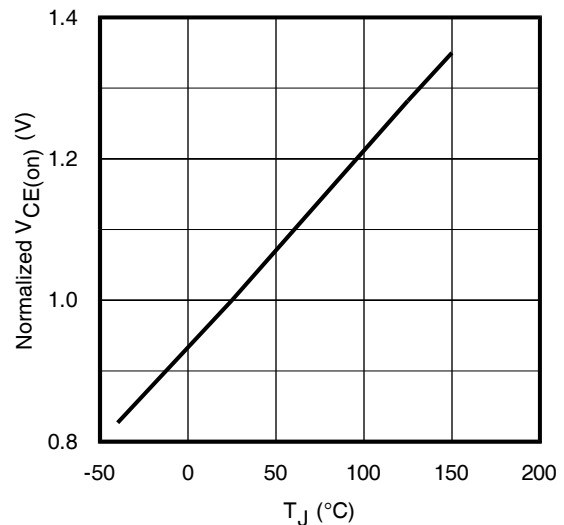
**Fig. 12 - Typ. Switching Time vs.  $I_C$**   
 $T_J = 125^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 390V$ ,  $R_G = 3.3\Omega$ ;  $V_{GE} = 15V$ .  
 Diode clamp used: 30ETH06 (See C.T.3)

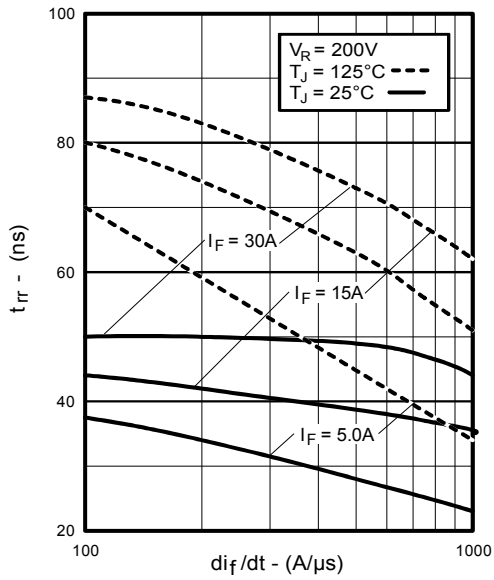
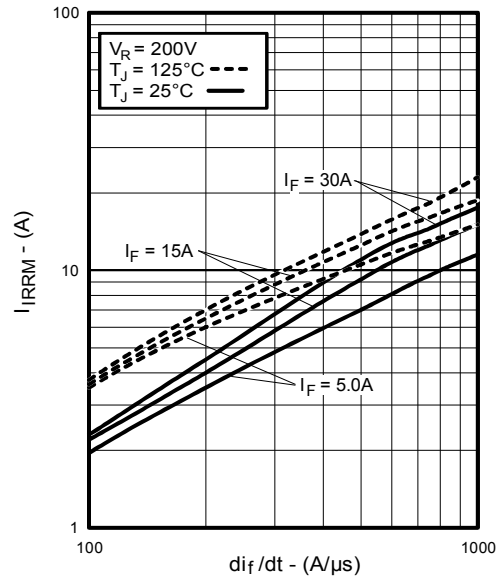
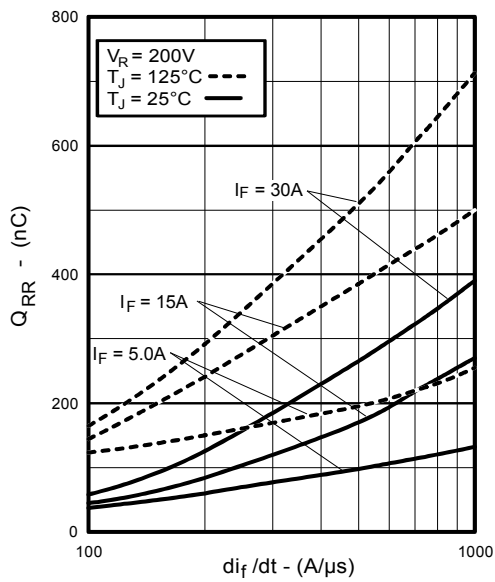
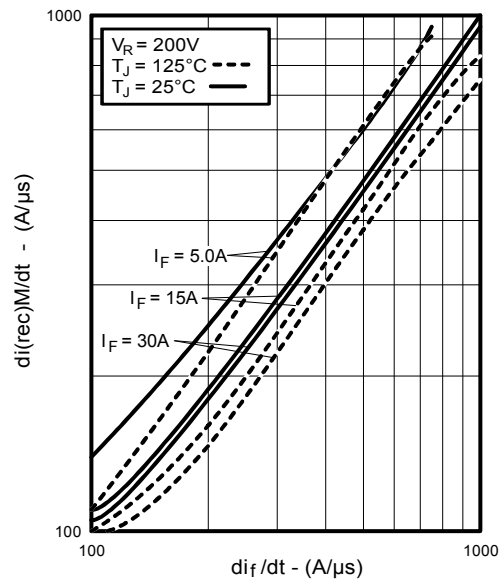

**Fig. 13 - Typ. Energy Loss vs.  $R_G$** 

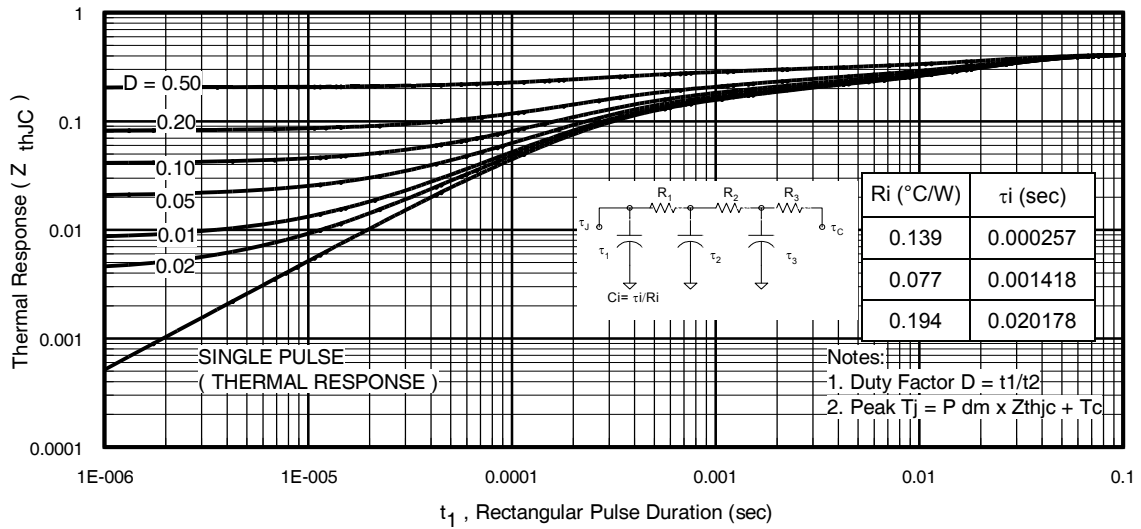
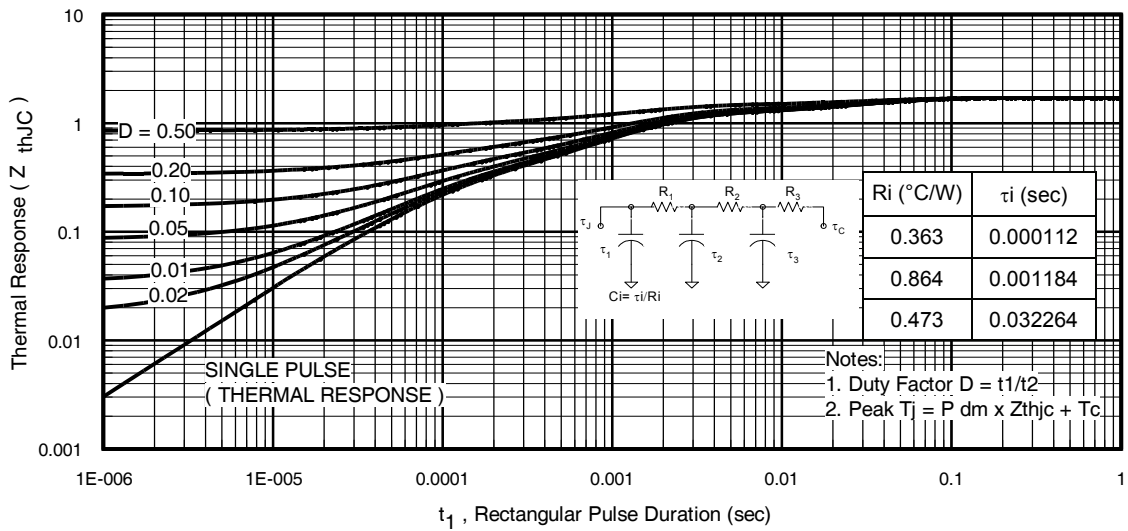
$T_J = 125^\circ\text{C}$ ;  $L = 200\mu\text{H}$ ;  $V_{CE} = 390\text{V}$ ,  $I_{CE} = 22\text{A}$ ;  $V_{GE} = 15\text{V}$   
Diode clamp used: 30ETH06 (See C.T.3)

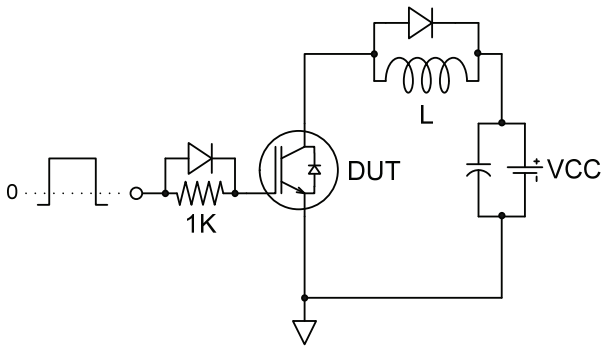
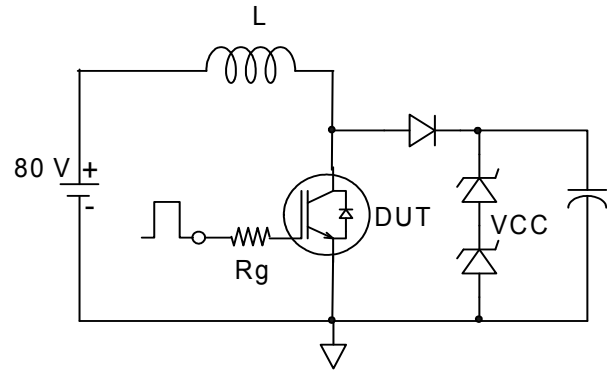
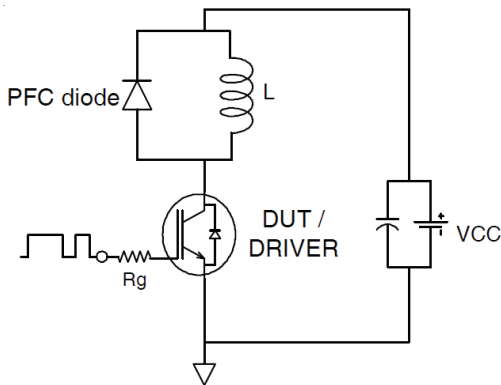
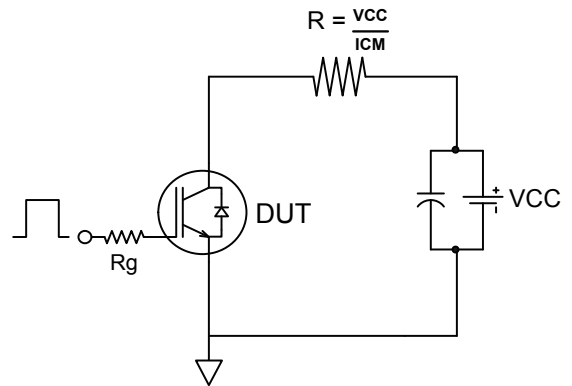
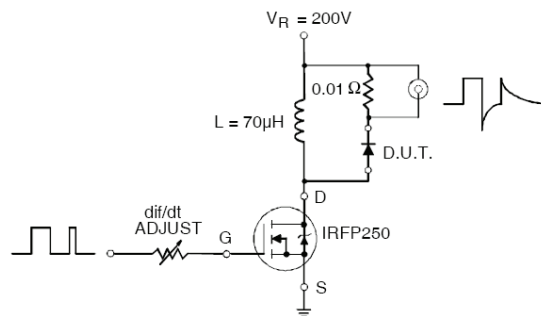

**Fig. 14 - Typ. Switching Time vs.  $R_G$** 

$T_J = 125^\circ\text{C}$ ;  $L = 200\mu\text{H}$ ;  $V_{CE} = 390\text{V}$ ,  $I_{CE} = 22\text{A}$ ;  $V_{GE} = 15\text{V}$   
Diode clamp used: 30ETH06 (See C.T.3)

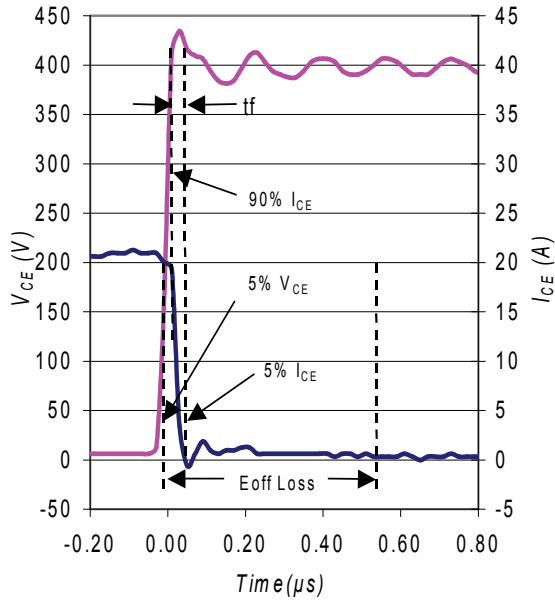

**Fig. 15 - Typ. Output Capacitance Stored Energy vs.  $V_{CE}$** 

**Fig. 16 - Typ. Capacitance vs.  $V_{CE}$**   
 $V_{GE} = 0\text{V}$ ;  $f = 1\text{MHz}$ 

**Fig. 17 - Typical Gate Charge vs.  $V_{GE}$**   
 $I_{CE} = 22\text{A}$ 

**Fig. 18 Normalized Typ.  $V_{CE(on)}$  vs. Junction Temperature**  
 $I_C = 22\text{A}$ ,  $V_{GE} = 15\text{V}$


**Fig. 19 - Typical Reverse Recovery vs.  $di/dt$** 

**Fig. 20 - Typical Recovery Current vs.  $di/dt$** 

**Fig. 21 - Typical Stored Charge vs.  $di/dt$** 

**Fig. 22 - Typical  $di(rec)M/dt$  vs.  $di/dt$ ,**

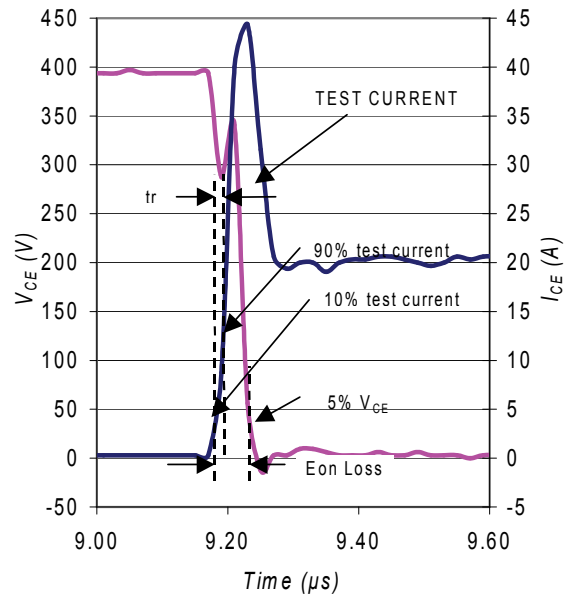

**Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)**

**Fig 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)**


**Fig.C.T.1 - Gate Charge Circuit (turn-off)**

**Fig.C.T.2 - RBSOA Circuit**

**Fig.C.T.3 - Switching Loss Circuit**

**Fig.C.T.4 - Resistive Load Circuit**
**REVERSE RECOVERY CIRCUIT**

**Fig.C.T.5 - Reverse Recovery Parameter Test Circuit**

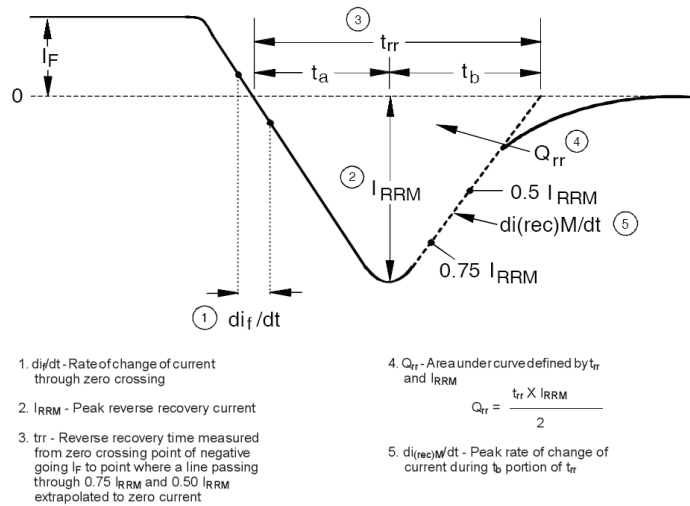




**Fig. WF1** - Typ. Turn-off Loss Waveform  
@  $T_J = 25^\circ\text{C}$  using Fig. CT.3



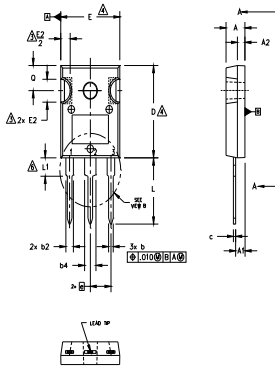
**Fig. WF2** - Typ. Turn-on Loss Waveform  
@  $T_J = 25^\circ\text{C}$  using Fig. CT.3



**Fig. WF3** - Reverse Recovery Waveform and Definitions

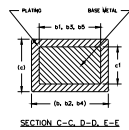
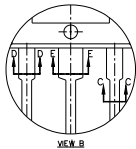
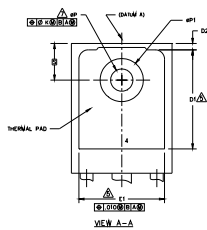
# TO-247AC Package Outline

(Dimensions are shown in millimeters (inches))



**NOTES:**

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .



SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

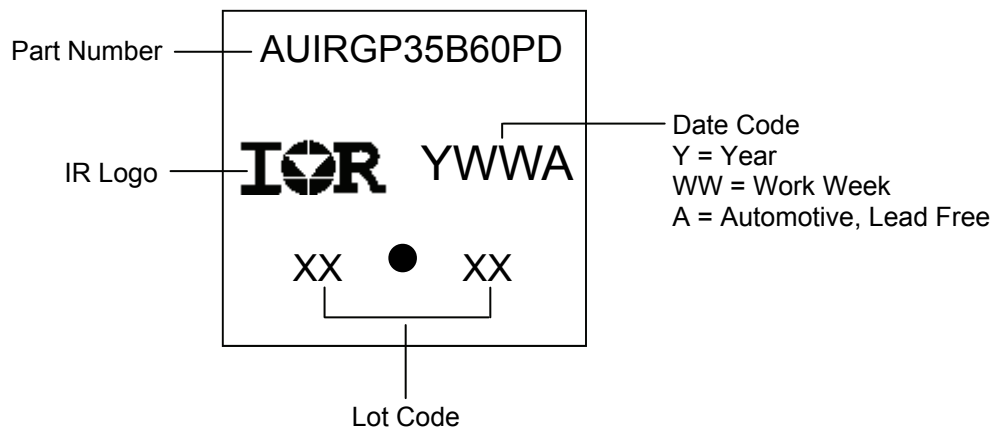
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

**DIODES**

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

## TO-247AC Part Marking Information



TO-247AC package is not recommended for Surface Mount Application.

**Qualification Information**

<b>Qualification Level</b>	Automotive (per AEC-Q101)	
	This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>	TO-247	N/A
<b>ESD</b>	Machine Model	Class M4(+/- 425V) <sup>†</sup> AEC-Q101-002
	Human Body Model	Class H2(+/- 4000V) <sup>†</sup> AEC-Q101-001
	Charged Device Model	Class C5 (+/- 1125V) <sup>†</sup> AEC-Q101-005
<b>RoHS Compliant</b>	Yes	

† Highest passing voltage.

**Revision History**

Date	Comments
8/24/2017	<ul style="list-style-type: none"> <li>Updated datasheet with corporate template</li> <li>Corrected typo Qual table -Moisture Sensitivity Level-from "MSL1" to N/A-page 11</li> <li>Corrected part marking on pages 10</li> </ul>

**Published by**

**Infineon Technologies AG**  
81726 München, Germany

© Infineon Technologies AG 2015

All Rights Reserved.

**IMPORTANT NOTICE**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office ([www.infineon.com](http://www.infineon.com)).

**WARNINGS**

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)